

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Shigeru NAGASAKA, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE INCLUDING MOS TRANSISTORS EACH HAVING A FLOATING GATE AND A CONTROL GATE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment form is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



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22850

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241723US2S			SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Shigeru NAGASAKA, et al.				
				FILING DATE Herewith			GROUP	
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	AA							
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
	AO							
	AP							
	AQ							
	AR							
	AS							
	AT							
	AU							
	AV							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
	AW	M. Togo, et al., "Low-Leakage and Highly-Reliable 1.5nm SiON Gate-Dielectric Using Radical Oxynitridation for Sub-0.1µm CMOS", Silicon Systems Research Labs., NEC.C (Japan), 2000 SYMPOSIUM ON VLSI TECHNOLOGY DIGEST OF TECHNICAL PAPERS, 2000, pgs. 116-117						
	AX	Wei-Hua Liu, et al., "A-2 Transistor Source-select (2TS) Flash EEPROM for 1.8V-Only Applications", Semiconductor Technologies Laboratory, Motorola Inc., Austin, Texas, NON-VOLATILE SEMICONDUCTOR MEMORY WORKSHOPS 4.1, 1997, pgs. 1-3						
	AY							
	AZ						<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
234863US2S	10/382,772	03/07/03	ARAI et al.